MICROWAVE POWER GAN HEMT TGI5867-60LHA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

·BROAD BAND INTERNALLY MATCHED HEMT

·HIGH POWER

Pout= 48.0dBm at Pin= 40dBm

·HIGH GAIN

GL= 12.5dB at Pin= 20dBm

 $\cdot \text{LOW}$ INTERMODULATION DISTORTION WITH WIDE SPACING TONE

IM3= -25dBc(Min.) at Pout= 41dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 40V IDSset= 0.4A f= 5.85 to 6.75GHz @Pin= 40dBm	dBm	47.0	48.0	
Drain Current	IDS1		А		3.5	4.5
Power Added Efficiency	ηadd		%		38	_
Linear Gain	GL	@Pin= 20dBm	dB	11.5	12.5	_
Gain flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	- Two-Tone Test Po= 41dBm - (Single Carrier Level) Δf= 5MHz (IM3) Δf= 150MHz (IM3-2)	dBc	-25	-30	_
	IM3-2		dBc	-25	-27	_
Drain Current	IDS2		А		2.0	2.5
Channel Temperature Rise *1	∆Tch		°C		120	140

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 10 Ω

*1: $\Delta Tch = (VDS \times IDS2 + Pin(two-tone)) - Po(two-tone)) \times Rth(c-c)$, calculated using parameters of IM3 test

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	_	4.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 15mA	V	-2.0	-3.0	-5.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А		10	
Gate-Source Breakdown Voltage	VGSO	IGS= -12mA	V	-10	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.6	1.8

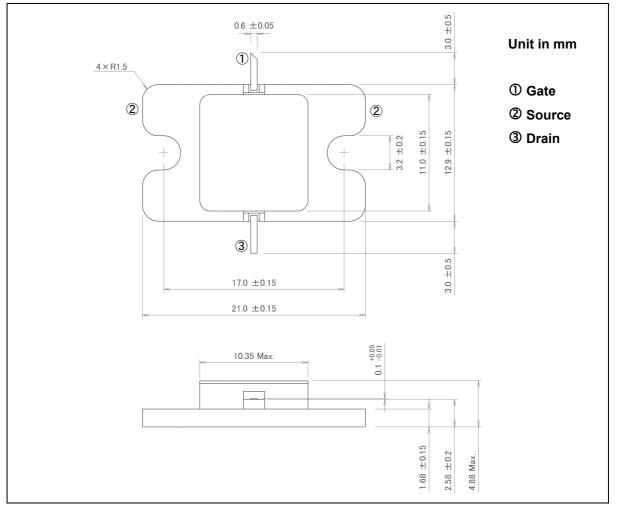
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	6.0
Total Power Dissipation (Tc= 25 °C)	PT	W	111
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA04A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

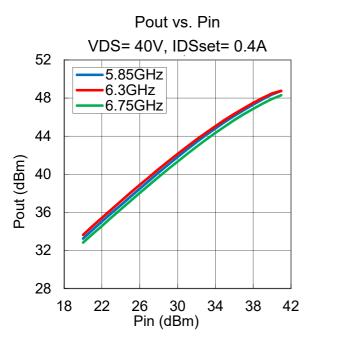
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

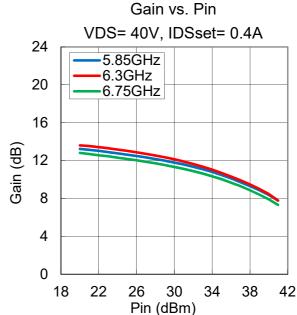
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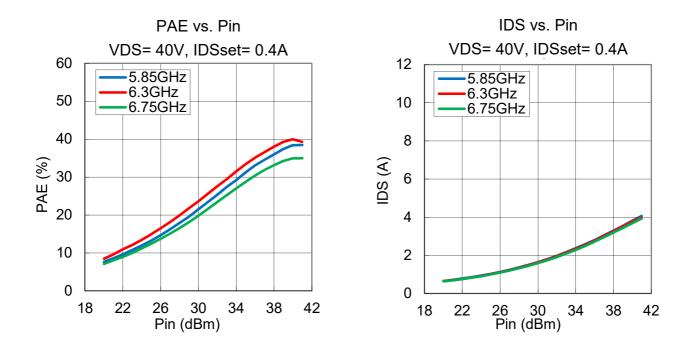
TYPICAL RF PERFORMANCE

·Pout, Gain, PAE, IDS vs. Pin

VDS= 40V, IDSset= 0.4A, f= 5.85, 6.3, 6.75GHz, Ta= +25°C



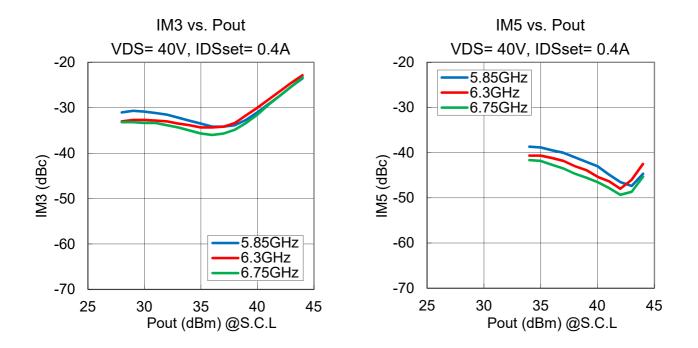




MICROWAVE SEMICONDUCTOR TECHNICAL DATA

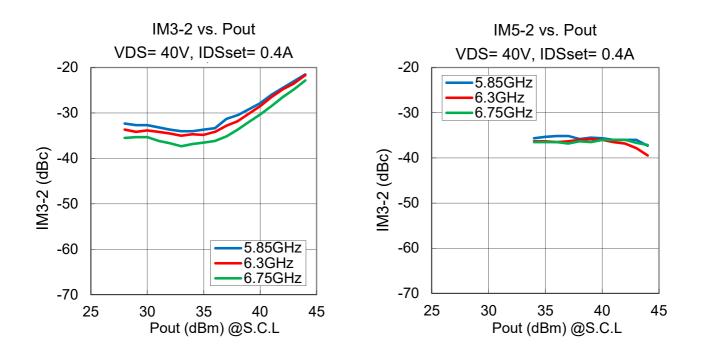
·IM3, IM5 vs. Pout

VDS= 40V, IDSset= 0.4A, f= 5.85, 6.3, 6.75GHz, ∆f= 5MHz, Ta= +25°C



·IM3-2, IM5-2 vs. Pout

VDS= 40V, IDSset= 0.4A, f= 5.85, 6.3, 6.75GHz, ∆f= 150MHz, Ta= +25°C

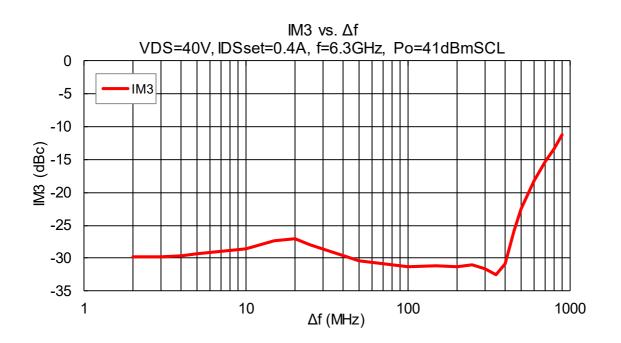




MICROWAVE SEMICONDUCTOR TECHNICAL DATA

IM3 vs. ∆f (Two tone spacing)

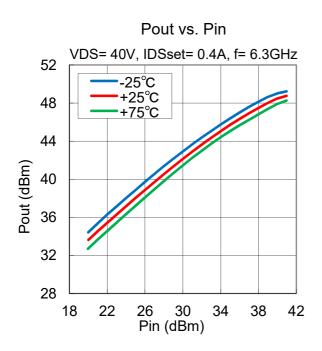
VDS= 40V, IDSset= 0.4A, f= 6.3GHz, Po= 41dBmSCL, Ta= +25°C

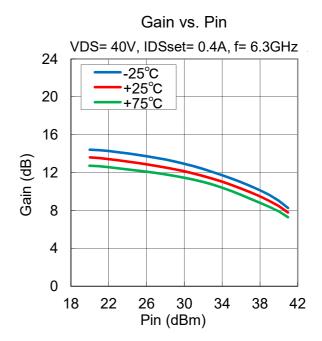


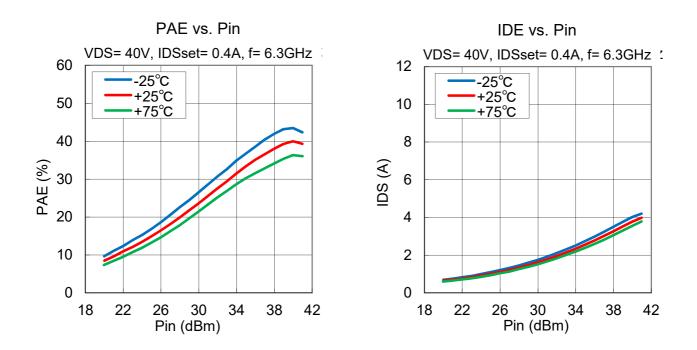
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 40V, IDSset= 0.4A, f= 6.3GHz, Ta= -25, +25, +75°C



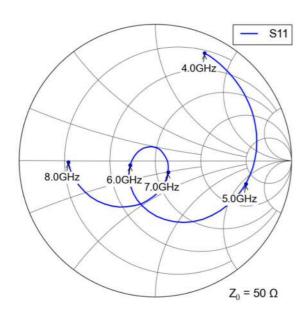


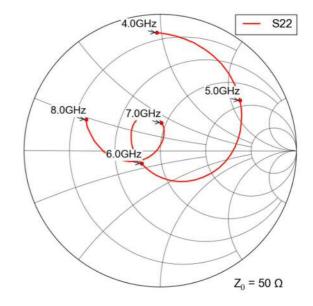


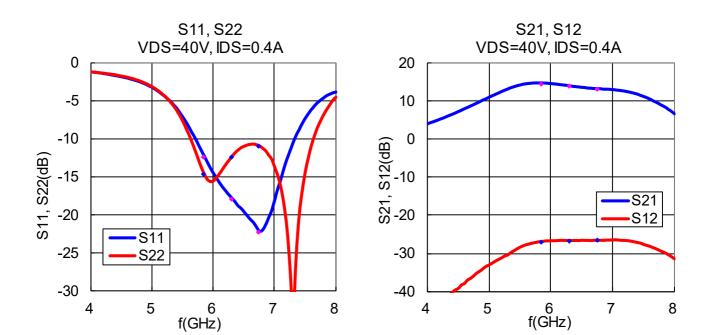
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 40 V, IDSset= 0.4 A, f= 4.0 to 8.0 GHz, Ta= +25 °C







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